

### **AMENDMENTS TO THE CLAIMS**

This listing of claims will replace all prior versions, and listings, of claims in the present application.

#### **Listing of Claims:**

**Claim 1 (original):** A III nitride single-crystal manufacturing method wherein a liquid layer of 200  $\mu\text{m}$  or less thickness is formed in between a substrate and a III nitride source-material baseplate, and III nitride single crystal is grown onto the face of said substrate on its liquid-layer side.

**Claim 2 (original):** A III nitride single-crystal manufacturing method set forth in claim 1, wherein said substrate in at least a superficial layer along the liquid layer is formed of a III nitride single crystal, and said III nitride source-material baseplate is formed of a III nitride polycrystal.

**Claim 3 (original):** A III nitride single-crystal manufacturing method set forth in claim 1, wherein said substrate in at least a superficial layer along the liquid layer, and said III nitride source-material baseplate are formed of a III nitride single crystal, and the face of said substrate on its liquid-layer side is a Group-III-atom surface; and the face of said III nitride source-material baseplate on its liquid-layer side is a nitrogen-atom surface.

**Claim 4 (previously presented):** A III nitride single-crystal manufacturing method set forth in claim 1, wherein said liquid layer includes an element of at least one kind selected from the group consisting of elements constituting said III nitride single crystal.

**Claims 5 and 6 (canceled)**